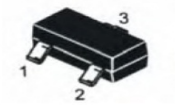
RoHS

BAS16

SOT-23 Plastic-Encapsulate DIODE

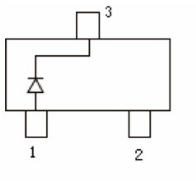
BAS16 **SWITCHING DIODE**

SOT-23



FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



Marking: A6

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	100	V
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Peak forward surge current @=1.0μs @=1.0s	I_{FSM}	2.2 1.0	A
Power Dissipation	P_D	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction temperature	Tj	150	°C
Storage temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	I_R= 100μA	75		V
Reverse voltage leakage current	I_R	V_R=75V		1	μA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		0.715 0.855 1 1.25	V
Diode capacitance	C_D	V_R=0, f=1MHz		2	pF
Reverse recovery time	t_{rr}	I_F=I_R=10mA,I_{rr}=0.1×I_R, R_L=100Ω		6	nS

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DEKRA Certification Inc.
AS9100C and ISO 9001:2008
Certificate No. 131519.01

Typical Characteristics

BAS16

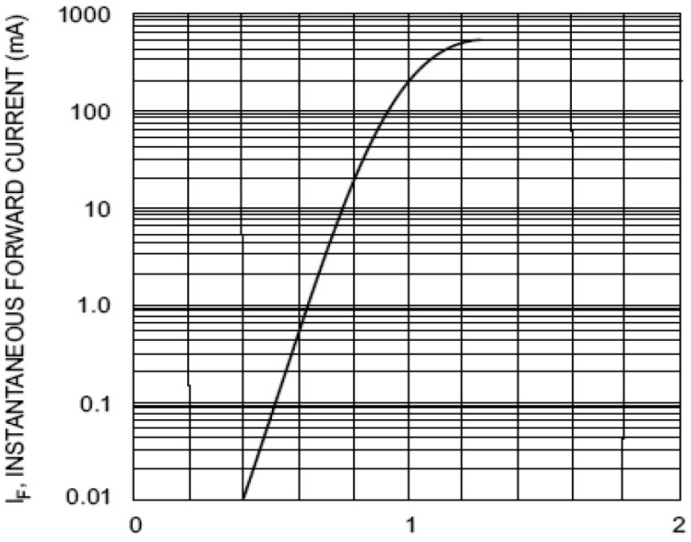

Fig. 1 Forward Characteristics

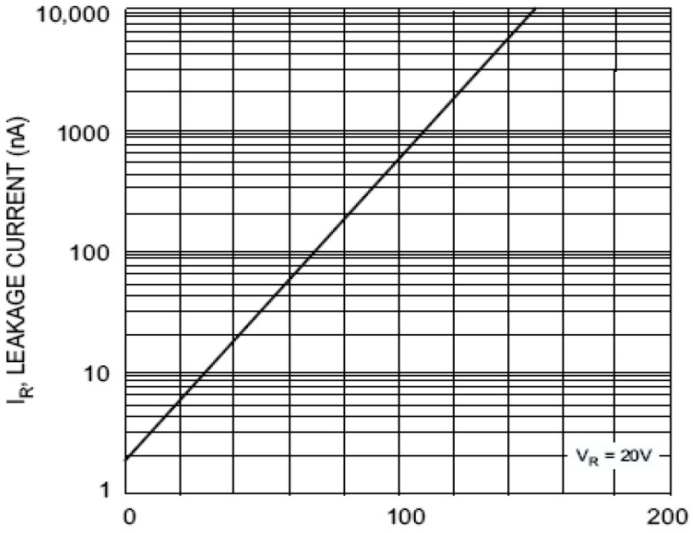

Fig. 2 Leakage Current vs Junction Temperature

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